

# NCP432, NCP433

## 1.5A Ultra-Small Controlled Load Switch with Auto-Discharge Path

The NCP432 and NCP433 are a low  $R_{on}$  MOSFET controlled by external logic pin, allowing optimization of battery life, and portable device autonomy.

Indeed, due to a current consumption optimization with PMOS structure, leakage currents are eliminated by isolating connected IC's on the battery when not used.

Output discharge path is also embedded to eliminate residual voltages on the output (NCP433 only).

Proposed in wide input voltage range from 1.0 V to 3.6 V, and a very small 0.76 x 0.76 mm WLCSP4, 0.4 mm pitch.

### Features

- 1 V – 3.6 V Operating Range
- 50 mΩ P MOSFET at 1.8 V
- DC Current up to 1.5 A
- Output Auto-discharge (NCP433)
- Active High EN Pin
- WLCSP4 0.76 x 0.76 mm
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Typical Applications

- Mobile Phones
- Tablets
- Digital Cameras
- GPS
- Portable Devices



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### MARKING DIAGRAM

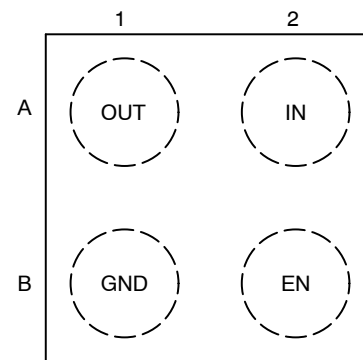


WLCSP4  
CASE 567FJ



XX = AV or AT

### PINOUT



(Top View)

### ORDERING AND MARKING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

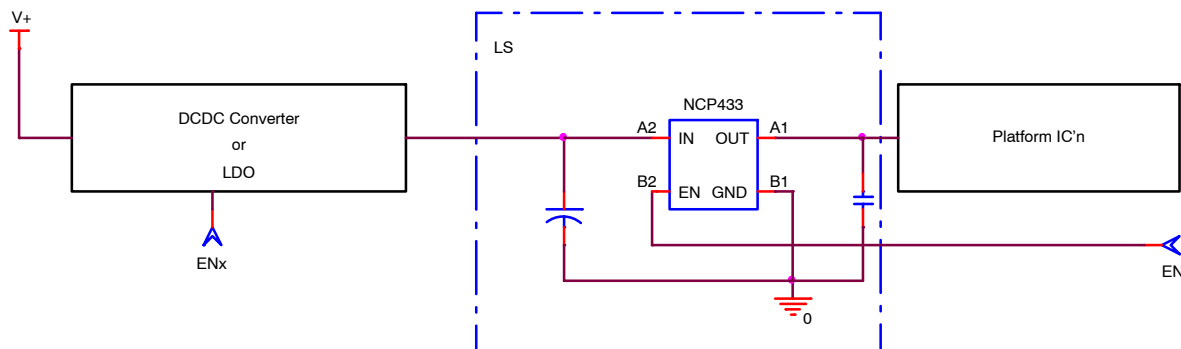


Figure 1. Typical Application Circuit

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## PIN FUNCTION DESCRIPTION

Pin Name	Pin Number	Type	Description
IN	A2	POWER	Load-switch input voltage; connect a 1 $\mu$ F or greater ceramic capacitor from IN to GND as close as possible to the IC.
GND	B1	POWER	Ground connection.
EN	B2	INPUT	Enable input, logic high turns on power switch.
OUT	A1	OUTPUT	Load-switch output; connect a 1 $\mu$ F ceramic capacitor from OUT to GND as close as possible to the IC is recommended.

## BLOCK DIAGRAM

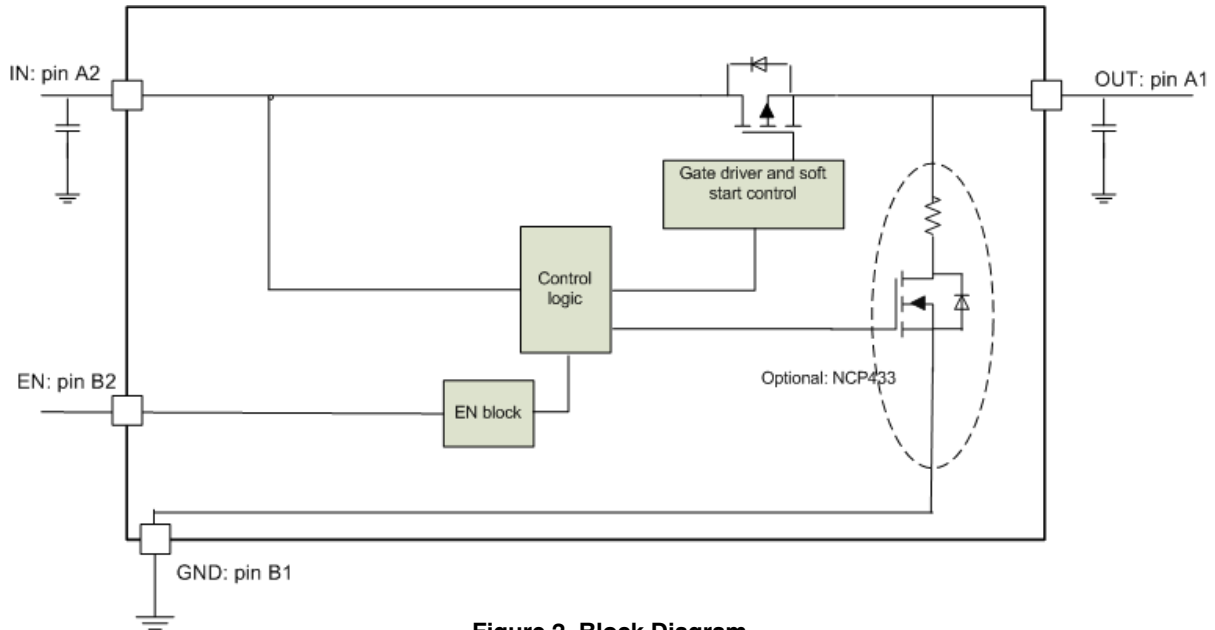


Figure 2. Block Diagram

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## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IN, OUT, EN, Pins:	$V_{EN}, V_{IN}, V_{OUT}$	-0.3 to + 4.0	V
From IN to OUT Pins: Input/Output	$V_{IN}, V_{OUT}$	0 to + 4.0	V
Maximum Junction Temperature	$T_J$	-40 to + 125	°C
Storage Temperature Range	$T_{STG}$	-40 to + 150	°C
Human Body Model (HBM) ESD Rating are (Notes 1 and 2)	ESD HBM	7000	V
Machine Model (MM) ESD Rating are (Notes 1 and 2)	ESD MM	250	V
Charge Device Model (CDM) ESD Rating are (Notes 1 and 2)	ESD CDM	2000	V
Latch-up protection (Note 3) – Pins IN, OUT, EN	LU	100	mA
Moisture Sensitivity (Note 4)	MSL	Level 1	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- According to JEDEC standard JESD22-A108.
- This device series contains ESD protection and passes the following tests:  
Human Body Model (HBM)  $\pm 7.0$  kV per JEDEC standard: JESD22-A114 for all pins.  
Machine Model (MM)  $\pm 250$  V per JEDEC standard: JESD22-A115 for all pins.  
Charge Device Model (CDM)  $\pm 2.0$  kV per JEDEC standard: JESD22-C101 for all pins.
- Latch up Current Maximum Rating:  $\pm 100$  mA per JEDEC standard: JESD78 class II.
- Moisture Sensitivity Level (MSL): 1 per IPC/JEDEC standard: J-STD-020.

## OPERATING CONDITIONS

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$V_{IN}$	Operational Power Supply			1.0		3.6	V
$V_{EN}$	Enable Voltage			0		3.6	
$T_A$	Ambient Temperature Range			-40	25	+85	°C
$C_{IN}$	Decoupling input capacitor			1			$\mu F$
$C_{OUT}$	Decoupling output capacitor			1			$\mu F$
$R_{\theta JA}$	Thermal Resistance Junction to Air	WLCSP package (Note 5)			150		°C/W
$I_{OUT}$	Maximum DC current					1.5	A
$P_D$	Power Dissipation Rating (Note 6)	$T_A \leq 25^\circ C$	WLCSP package		0.5		W
		$T_A = 85^\circ C$	WLCSP package		0.2		W

- The  $R_{\theta JA}$  is dependent of the PCB heat dissipation and thermal via.
- The maximum power dissipation ( $P_D$ ) is given by the following formula:

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**ELECTRICAL CHARACTERISTICS** Min & Max Limits apply for  $T_A$  between  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  for  $V_{IN}$  between 1.0 V to 3.6 V (Unless otherwise noted). Typical values are referenced to  $T_A = +25^{\circ}\text{C}$  and  $V_{IN} = 3.3\text{ V}$  (Unless otherwise noted).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit		
<b>POWER SWITCH</b>								
$R_{DS(on)}$	Static drain-source on-state resistance	$V_{IN} = 3.6\text{ V}$	$T_A = 25^{\circ}\text{C}, I = 200\text{ mA}$ (Note 8)		35		m $\Omega$	
			$T_A = 85^{\circ}\text{C}$			55		
		$V_{IN} = 3.3\text{ V}$	$T_A = 25^{\circ}\text{C}, I = 200\text{ mA}$		37			
			$T_A = 85^{\circ}\text{C}$			60		
		$V_{IN} = 1.8\text{ V}$	$T_A = 25^{\circ}\text{C}, I = 200\text{ mA}$		50			
			$T_A = 85^{\circ}\text{C}$			80		
		$V_{IN} = 1.2\text{ V}$	$T_A = 25^{\circ}\text{C}, I = 200\text{ mA}$		100			
			$T_A = 85^{\circ}\text{C}$			150		
$V_{IN} = 1.1\text{ V}$	$T_A = 25^{\circ}\text{C}, I = 100\text{ mA}$		120					
$R_{DIS}$	Output discharge path	EN = low	$V_{IN} = 3.3\text{ V}$ , NCP433 only	40	65	90	$\Omega$	
$T_R$	Output rise time	$V_{IN} = 3.6\text{ V}$	$C_{LOAD} = 1\text{ }\mu\text{F}, R_{LOAD} = 25\text{ }\Omega$ (Note 7) from 10% to 90% of $V_{OUT}$	5	20	40	$\mu\text{s}$	
$T_F$	Output fall time			20	56	80	$\mu\text{s}$	
$T_{on}$	Gate turn on			Gate turn on + Output rise time	20	47	115	$\mu\text{s}$
$T_{en}$	Enable time			From EN low to high to $V_{OUT} 10\%$	15	30	75	$\mu\text{s}$
$T_{dis}$	Disable time			From EN high to low to $V_{OUT} = 90\%$ of fully on	2	11	20	$\mu\text{s}$
$V_{IH}$	High-level input voltage		0.9			V		
$V_{IL}$	Low-level input voltage				0.5	V		

## QUIESCENT CURRENT

$I_Q$	Current consumption	$V_{IN} = 3.3\text{ V}$ , EN = low, No load		0.01	0.6	$\mu\text{A}$
		$V_{IN} = 3.3\text{ V}$ , EN = high, No load		0.2	0.6	$\mu\text{A}$

7. Parameters are guaranteed for  $C_{LOAD}$  and  $R_{LOAD}$  connected to the OUT pin with respect to the ground  
 8. Guaranteed by design and characterization, not production tested.

## TIMINGS

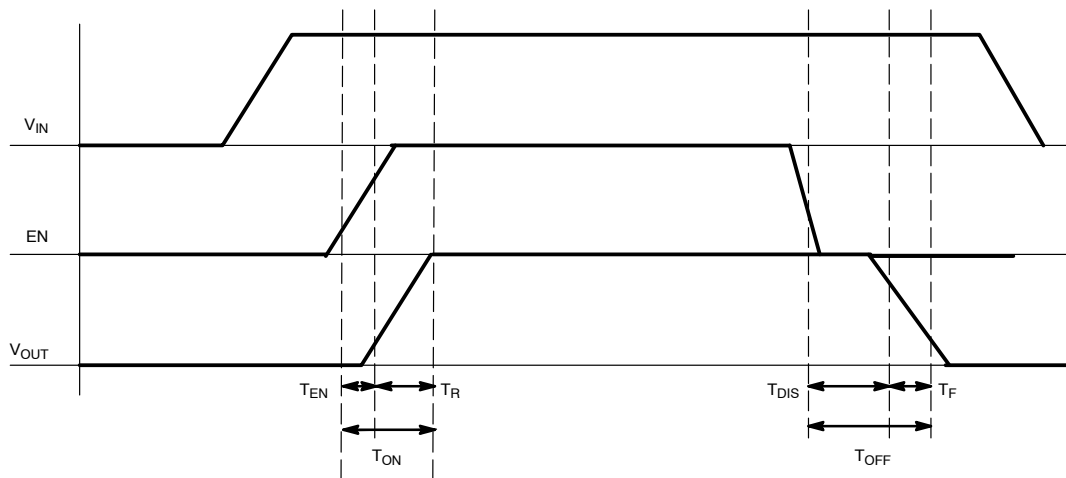


Figure 3. Enable, Rise and Fall Time

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## TYPICAL CHARACTERISTICS

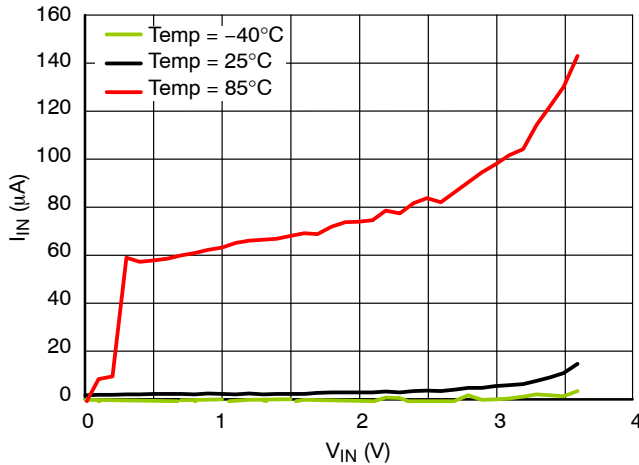


Figure 4. Standby Current versus Temperature

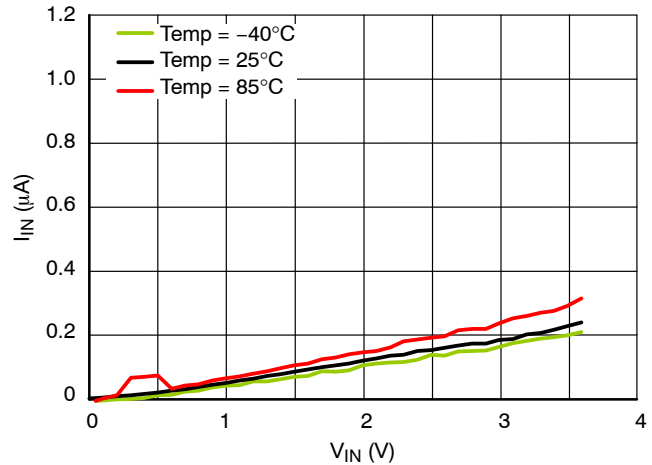


Figure 5. Quiescent Current versus Temperature

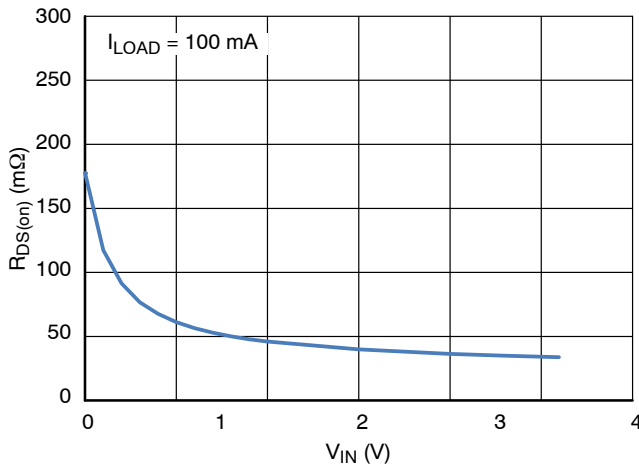


Figure 6.  $R_{DS(on)}$  versus  $V_{IN}$ , 25°C, 100 mA Load

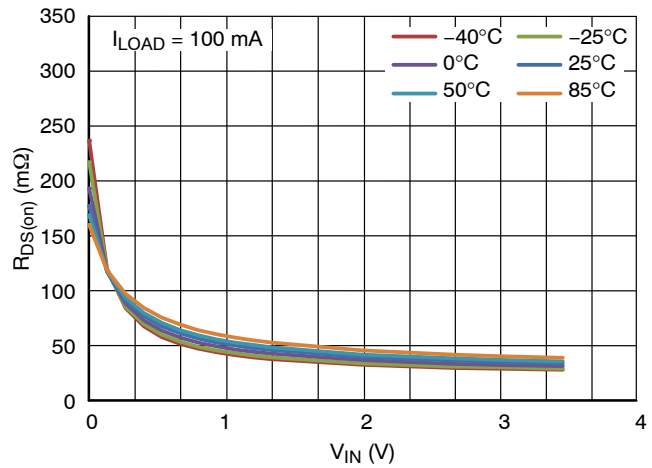


Figure 7.  $R_{DS(on)}$  versus Temperature, 100 mA Load

## FUNCTIONAL DESCRIPTION

### Overview

The NCP432 – NCP433 are high side P channel MOSFET power distribution switch designed to isolate ICs connected on the battery in order to save energy. The part can be turned on, with a range of battery from 1.0 V to 3.6 V.

### Enable Input

Enable pin is an active high. The path is opened when EN pin is tied low (disable), forcing P MOS switch off.

The IN/OUT path is activated with a minimum of  $V_{in}$  of 1.0 V and EN forced to high level.

### Auto Discharge (NCP433 only)

NMOS FET is placed between the output pin and GND, in order to discharge the application capacitor connected on OUT pin.

The auto-discharge is activated when EN pin is set to low level (disable state).

The discharge path ( Pull down NMOS) stays activated as long as EN pin is set at low level and  $V_{IN} > 1.0$  V.

In order to limit the current across the internal discharge N-MOSFET, the typical value is set at 65  $\Omega$ .

### Cin and Cout Capacitors

IN and OUT, 1  $\mu$ F, at least, capacitors must be placed as close as possible the part for stability improvement.

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## APPLICATION INFORMATION

### Power Dissipation

Main contributor in term of junction temperature is the power dissipation of the power MOSFET. Assuming this, the power dissipation and the junction temperature in normal mode can be calculated with the following equations:

$$P_D = R_{DS(on)} \times (I_{OUT})^2$$

$P_D$  = Power dissipation (W)  
 $R_{DS(on)}$  = Power MOSFET on resistance ( $\Omega$ )  
 $I_{OUT}$  = Output current (A)

$$T_J = P_D \times R_{\theta JA} + T_A$$

$T_J$  = Junction temperature ( $^{\circ}\text{C}$ )  
 $R_{\theta JA}$  = Package thermal resistance ( $^{\circ}\text{C}/\text{W}$ )  
 $T_A$  = Ambient temperature ( $^{\circ}\text{C}$ )

### PCB Recommendations

The NCP432 – NCP433 integrate an up to 1.5 A rated PMOS FET, and the PCB design rules must be respected to properly evacuate the heat out of the silicon. By increasing PCB area, especially around IN and OUT pins, the  $R_{\theta JA}$  of the package can be decreased, allowing higher power dissipation.

## ORDERING INFORMATION

Device	Marking	Package	Shipping†
NCP432FCT2G	AV	WLCSP4 (Pb-Free)	3000 / Tape & Reel
NCP433FCT2G	AT	WLCSP4 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

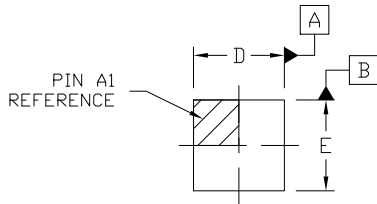
# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



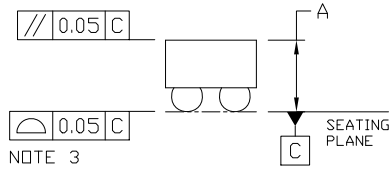
SCALE 4:1

WLCSP4, 0.76x0.76  
CASE 567FJ  
ISSUE A

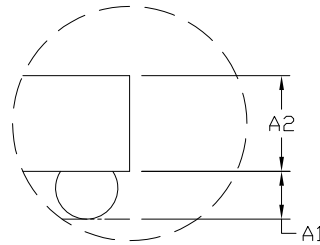
DATE 08 MAR 2022



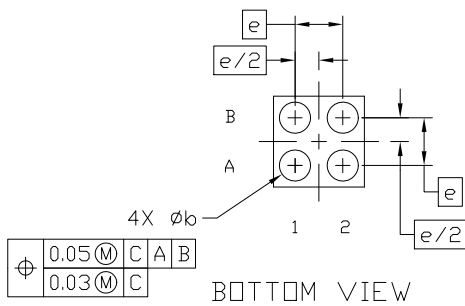
TOP VIEW



SIDE VIEW



SIDE VIEW  
SCALE 1:2

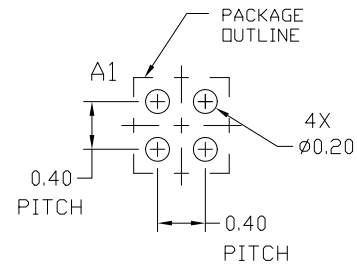


BOTTOM VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE SPHERICAL CROWNS OF THE SOLDER BALLS.

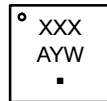
DIM	MILLIMETERS	
	MIN.	MAX.
A	0.57	0.63
A1	0.18	0.23
A2	0.40 REF.	
b	0.24	0.28
D	0.73	0.79
E	0.73	0.79
e	0.40 BSC	



RECOMMENDED  
MOUNTING FOOTPRINT\*

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

**GENERIC MARKING DIAGRAM\***



- XXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>WLCSP4, 0.76x0.76</b>	<b>PAGE 1 OF 1</b>

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